

# 1024K (128K x 8) CMOS UV EPROM - OTP ROM

- INTERCHANGEABLE WITH 1M BIT MASKED ROM (ROM PIN OUT).
- VERY FAST ACCESS TIME: 120ns.
- COMPATIBLE WITH HIGH SPEED MICRO-PROCESSORS, ZERO WAIT STATE.
- LOW "CMOS" POWER COMSUMPTION:
  - Active Current 35 mA
  - Standby Current 200 μA
- PROGRAMMING VOLTAGE 12.75V.
- ELECTRONIC SIGNATURE FOR AUTOMATED PROGRAMMING.
- PROGRAMMING TIMES AROUND 12 SEC-ONDS (PRESTO II ALGORITHM).

## **DESCRIPTION**

The M27C1000 is a high speed 1 Mbit ultraviolet erasable and electrically programmable EPROM ideally suited for 8-bit microprocessor systems requiring large programs.

It is pin compatible with 1Mbit Masked ROM version, when EPROM memory is only to be used for pre-production series.

It is organized as 131,072 words by 8 bits, and housed in a 32 pin window Ceramic Frit-Seal package.

The transparent lid allows the user to expose the chip to ultraviolet light to erase the bit pattern. A new pattern can then be written to the device by following the programming procedure.

In order to meet production requirements (cost effective solution or SMD), this product is also offered in a plastic package, either Plastic DIP or PLCC, for one time programming only.

#### **PIN FUNCTIONS**

A0-A16	ADDRESS INPUT
CE	CHIP ENABLE
OE	OUTPUT ENABLE
PGM	PROGRAM
O0-O7	DATA INPUT/OUTPUT
NC	NO CONNECTION
Vcc	+5V POWER SUPPLY
V <sub>PP</sub>	PROGRAMMING VOLTAGE

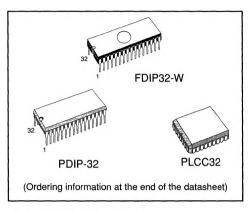


Figure 1: Pin Connection

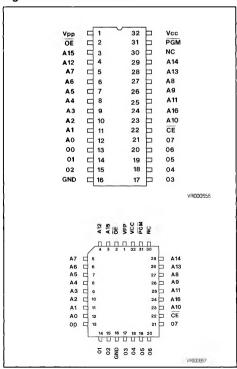
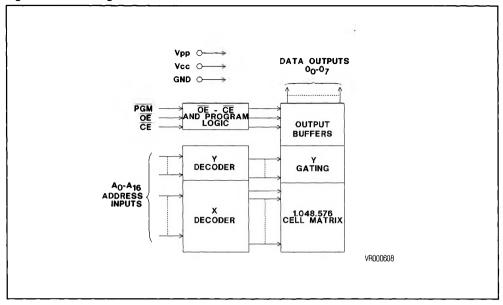


Figure 2: Block Diagram



## **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
Vi	Input or Output voltages with respect to ground	-0.6 to +7.0	V
V <sub>PP</sub>	Supply voltage with respect to ground	-0.6 to +14.0	V
V <sub>A9</sub>	Voltage on A9 with respect to ground	-0.6 to +13.5	V
Vcc	Supply voltage with respect to ground	-0.6 to +7.0	٧
T <sub>bias</sub>	Temperature range under bias	-50 to +125	°C
T <sub>stg</sub>	Storage temperature range	-65 to +150	°C

NOTE: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

#### **OPERATING MODES**

MODE			P	INS		
MODE	CE	OE	A9	PGM	V <sub>PP</sub>	OUTPUT
READ	L	L	Х	Х	Vcc	D <sub>out</sub>
OUTPUT DISABLE	L	Н	Х	Х	Vcc	HIGH Z
STANDBY	Н	Х	Х	X	Vcc	HIGH Z
PROGRAM	L	Х	X	L	V <sub>PP</sub>	DiN
PROGRAM VERIFY	L	L	Х	Н	V <sub>PP</sub>	D <sub>OUT</sub>
PROGRAM INHIBIT	Н	Х	X	X	V <sub>PP</sub>	HIGH Z
ELECTRONIC SIGNATURE	L	L	V <sub>H</sub>	Н	Vcc	CODE

NOTE : X = Don't care;  $V_H = 12V \pm 0.5V$ ; H = High; L = Low

## **READ OPERATION**

## DC AND AC CONDITIONS

SELECTION CODE	F1	F6	F7	F3
Operating Temperature Range	0 to +70°C	-40 to +85°C	-40 to +105°C	-40 to +125°C
SELECTION CODE (Example for 0°C to 70°C Oper. Temp. Range)	12XF1, 15XF1	, 20XF1, 25XF1	12F1, 15F1,	20F1, 25F1
Vcc	5 V :	± 5 %	5 V ±	10 %

NOTE: "F" stands for ceramic package. Plastic packaged device code features B,M or C

## DC AND OPERATING CHARACTERISTICS (F1 AND F6 DEVICES)

Symbol	Parameter	Test Condition	Val	Unit		
Symbol	raidilletei	rest Condition	Min	Max	Unit	
ILI	Input Leakage Current	V <sub>IN</sub> = 0V to V <sub>CC</sub>	-10	10	μА	
lo	Output Leakage Current	V <sub>IN</sub> = 0V to V <sub>CC</sub>	-10	10	μА	
l <sub>CC1</sub>	V <sub>CC</sub> Active Current	$\overrightarrow{CE} = \overrightarrow{OE} = \overrightarrow{VI_L}, I_{OUT} = 0 \text{ mA}$ $(F = 5 \text{ MHz})$		35	mA	
I <sub>CC2</sub>	V <sub>CC</sub> Standby Current - TTL	CE = V <sub>IH</sub>		1	mA	
Icc3 (4)	V <sub>CC</sub> Standby Current - CMOS	CE > V <sub>CC</sub> - 0.2 V		200	μΑ	
I <sub>PP1</sub>	V <sub>PP</sub> Read Current	V <sub>PP</sub> = V <sub>CC</sub>		10	μΑ	
V <sub>IL</sub>	Input Low Voltage		-0.3	0.8	٧	
V <sub>IH</sub>	Input High Voltage		2.0	V <sub>CC</sub> +1.0	٧	
V <sub>OL</sub>	Output Low Voltage	I <sub>OL</sub> = 2.1 mA		0.4	٧	
V <sub>OH</sub>	Output High Voltage	I <sub>OH</sub> = -400μA I <sub>OH</sub> = -100μA	2.4 V <sub>CC</sub> -0.7		٧	

## **AC CHARACTERISTICS**

			M27C1000								
Symbol	Parameter	Test condition	-12		-15		-20		-25		Unit
			Min	Max	Min	Max	Min	Max	Min	Max	
tacc	Address Output Delay	CE=OE=VIL		120		150		200		250	ns
tce	CE to Output Delay	OE=V <sub>IL</sub>		120		150		200		250	ns
toe	OE to Output Delay	CE=V <sub>IL</sub>		60		65		70		100	ns
t <sub>DF</sub> <sup>(2)</sup>	OE High to Output Float	CE=V <sub>IL</sub>	0	40	0	50	0	60	0	60	ns
tон	Output Hold from Address, CE or OE Whichever occured first	CE=OE=V <sub>IL</sub>	0		0		0		0		ns

# CAPACITANCE<sup>(3)</sup> (T<sub>A</sub> = 25°C, f = 1MHz)

Symbol	Parameter	Test Condition	Min	Тур	Max	Unit
CIN	Input Capacitance	V <sub>IN</sub> = 0V		4	6	pF
Соит	Output Capacitance	V <sub>OUT</sub> = 0V		8	12	pF

NOTES: 1. Vcc must be applied simultaneously or before VPP and removed simultaneously or after VPP.

This parameter is only sampled and not 100 % tested. Output Float is defined as the point where data is no longer driven (see timing diagram).

3. This parameter is only sampled and not 100 % tested.

4. From date code 9112.

#### **AC TEST CONDITIONS**

≤ 20 ns Input Rise and Fall Times Timing Measurement Reference Levels: Input Pulse Levels : 0.45 to 2.4V Inputs: 0.8 and 2V - Outputs: 0.8 and 2V

Figure 3: AC Testing Input/Output Waveform

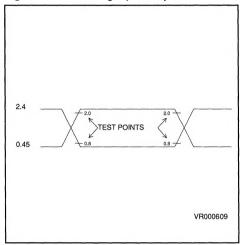


Figure 4: AC Testing Load Circuit

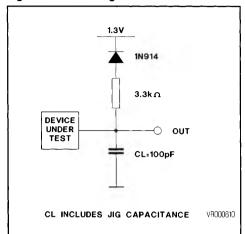
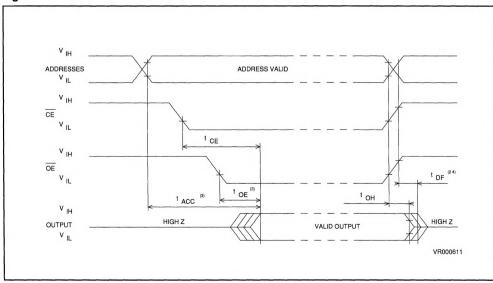


Figure 5 : AC Waveforms



NOTES: 1. Typical values are for TA = 25°C and nominal supply voltage.

This parameter is only sampled and not 100 % tested.
 DE may be delayed up to tce toe after the falling edge CE without impact on tce.
 The is specified from OE or CE whichever occurs first.

#### **DEVICE OPERATION**

The modes of operations of the M27C1000 are listed in the Operating Modes table. A single 5V power supply is required in the read mode. All inputs are TTL levels except for V<sub>PP</sub> and 12V on A9 for Electronic Signature.

#### **READ MODE**

The M27C1000 has two control functions, both of which must be logically active in order to obtain data at the outputs. Chip Enable (CE) is the power control and should be used for device selection. Output Enable (OE) is the output control and should be used to gate data to the output pins, independent of device selection. Assuming that the addresses are stable, the address access time (tACC) is equal to the delay from CE to output (tCE). Data is available at the output after delay of toe from the falling edge of OE, assuming that CE has been low and the addresses have been stable for at least tACC-tOE.

### STANDBY MODE

The M27C1000 has a standby mode which reduces the active current from 35 mA to 0.2 mA (from date code 9044). The M27C1000 is placed in the standby mode by applying a CMOS high signal to the CE input. When in the standby mode, the outputs are in a high impedance state, independent of the OE input.

#### TWO LINE OUTPUT CONTROL

Because EPROMs are usually used in larger memory arrays, the product features a 2 line control function which accommodates the use of multiple memory connection. The two line control function allows:

a) the lowest possible memory power dissipation,
 b) complete assurance that output bus contention will not occur.

For the most efficient use of these two control lines, CE should be decoded and used as the primary device selecting function, while OE should be made a common connection to all devices in the array and connected to the READ line from the system control bus. This ensures that all deselected memory devices are in their low power standby mode and that the output pins are only active when data is required from a particular memory device.

### SYSTEM CONSIDERATIONS

The power switching characteristics of CMOS-E4 EPROMs requires careful decoupling of the devices. The supply current, Icc, has three seg-

ments that are of interest to the system designer : the standby current level, the active current level, and transient current peaks that are produced by the falling and rising edges of CE. The magnitude of this transient current peaks is dependent on the output capacitive and inductive loading of the device. The associated transient voltage peaks can be suppressed by complying with the two line output control and by properly selected decoupling capacitors. It is recommended that a 1µF ceramic capacitor be used on every device between Vcc and GND. This should be a high frequency capacitor of low inherent inductance and should be placed as close to the device as possible. In addition, a 4.7µF bulk electrolytic capacitor should be used between Vcc. and GND for every eight devices. The bulk capacitor should be located near the power supply connection point. The purpose of the bulk capacitor is to overcome the voltage drop caused by the inductive effects of PCB traces.

#### **PROGRAMMING**

Caution: exceeding 14V on VPP pin will permanently damage the M27C1000.

When delivered (and after each erasure for UV EPROM), all bits of the M27C1000 are in the "1" state. Data is introduced by selectively programming "0s" into the desired bit locations. Although only "0s" will be programmed, both "1s" and "0s" can be present in the data word. The only way to change a "0" to a "1" is by die exposure to ultraviolet light (UV EPROM). The M27C1000 is in the programming mode when VPP input is at 12.75V, and CE and PGM are at TTL-low. The data to be programmed is applied 8 bits in parallel to the data output pins. The levels required for the address and data inputs are TTL. Vcc is specified to be 6.25V  $\pm$  0.25V.

# VERY FAST AND RELIABLE PROGRAMMING ALGORITHM = PRESTO II

PRESTO II Programming Algorithm allows the whole array to be programmed with a guaranteed margin, in a typical time of less than 12 seconds. Programming with PRESTO II consists of applying a sequence of 100 microseconds program pulses to each byte until a correct verify occurs. During programming and verify operation, a MARGIN MODE circuit is automatically activated in order to guarantee that each cell is programmed with enough margin. No overprogram pulse is applied since the verify in MARGIN MODE provides necessary margin to each programmed cell.

## **DEVICE OPERATION (Continued)**

#### PROGRAM INHIBIT

Programming of multiple M27C1000s in parallel with different data is also easily accomplished. Except for CE, all like inputs including OE of the parallel M27C1000 may be common. A TTL low level pulse applied to a M27C1000's CE input, with PGM low and  $V_{PP}$  at 12.75V, will program that M27C1000. A high level CE input inhibits the other M27C1000s from being programmed. Vcc is specified to be 6.25V  $\pm$  0.25V

#### PROGRAM VERIFY

A verify (read) should be performed on the programmed bits to determine that they were correctly programmed. The verify is accomplished with CE and OE at  $V_{\rm IL}$ , PGM at  $V_{\rm IH}$ ,  $V_{\rm PP}$  at 12.75V and  $V_{\rm CC}$  at 6.25V.

## **ELECTRONIC SIGNATURE**

The Electronic Signature mode allows the reading out of a binary code from an EPROM that will identify its manufacturer and type, this mode is intended for use by programming equipment to automatically match the device to be programmed with its corresponding programming algorithm. This mode is functional in the 25°C ± 5°C ambient temperature range that is required when programming the M27C1000. To activate this mode, the programming equipment must force 11.5V to 12.5V on address line A9 of the M27C1000 with  $V_{PP} = V_{CC} = 5V$ . Two identifier bytes may then be sequenced from the device outputs by toggling address line A0 from V<sub>II</sub> to VIH. All other address lines must be held at VIL during Electronic Signature mode. Byte 0

 $(A0=V_{IL})$  represents the manufacturer code and byte 1 (A0=V\_{IH}) the device identifier code. For the SGS-THOMSON M27C1000, these two identifier bytes are given here below, and can be read out on outputs O0 to 07.

# ERASURE OPERATION (applies for UV EPROM)

The erasure characteristics of the M27C1000 is such that erasure begins when the cells are exposed to light with wavelengths shorter than approximately 4000 Å. It should be noted that sunlight and some type of fluorescent lamps have wavelengths in the 3000-4000 Å range. search shows that constant exposure to room level fluorescent lighting could erase a typical M27C1000 in about 3 years, while it would take approximately 1 week to cause erasure when exposed to direct sunlight. If the M27C1000 is to be exposed to these types of lighting conditions for extended periods of time, it is suggested that opaque labels be put over the M27C1000 window to prevent unintentional erasure. The recommended erasure procedure for the M27C1000 is exposure to short wave ultraviolet light which has wavelength 2537 Å. The integrated dose (i.e. UV intensity X exposure time) for erasure should be a minimum of 15 W-sec/cm<sup>2</sup>. The erasure time with this dosage is approximately 15 to 20 minutes using an ultraviolet lamp with 12000 μW/cm<sup>2</sup> power rating. The M27C1000 should be placed within 2.5 cm (1 inch) of the lamp tubes during the erasure. Some lamps have a filter on their tubes which should be removed before erasure.

## **ELECTRONIC SIGNATURE MODE**

IDENTIFIER					PII	NS				
I DENTILLA	A0	07	O6	O5	04	О3	02	01	00	Hex
MANUFACTURER CODE	VIL	0	0	1	0	0	0	0	0	20
DEVICE CODE	ViH	1	0	0	0	0	1	1	0	86

NOTE : A9 = 12V  $\pm$  0.5V ;  $\overline{\text{CE}}$  =  $\overline{\text{OE}}$  = V<sub>1L</sub> , A1 - A8, A10 - A16 = V<sub>1L</sub> ; V<sub>PP</sub> = V<sub>CC</sub> = 5V

# PROGRAMMING OPERATION

 $(T_A = 25^{\circ}C \pm 5^{\circ}C, V_{CC}^{(1)} = 6.25V \pm 0.25V, V_{PP}^{(1)} = 12.75V \pm 0.25V)$ 

## DC AND OPERATING CHARACTERISTICS

Symbol	Parameter	Test Condition	Va	lues	Unit
	raiametei	(see note 1)	Min	Max	Onn
lu	Input Current (All Inputs)	VIN = VIL or VIH		10	μΑ
VIL	Input Low Level (All Inputs)		-0.1	0.8	٧
VIH	Input High Level		2.0	V <sub>CC</sub> +0.5	٧
V <sub>OL</sub>	Output Low Voltage During Verify	I <sub>OL</sub> = 2.1 mA		0.45	٧
V <sub>OH</sub>	Output High Voltage During Verify	I <sub>OH</sub> = -400µA	2.4		٧
I <sub>CC2</sub>	V <sub>CC</sub> Supply Current			50	mA
I <sub>PP2</sub>	V <sub>PP</sub> Supply Current (program)	CE = V <sub>IL</sub>		50	mA
V <sub>ID</sub>	A9 Electronic Signature Voltage		11.5	12.5	٧

## **AC CHARACTERISTICS**

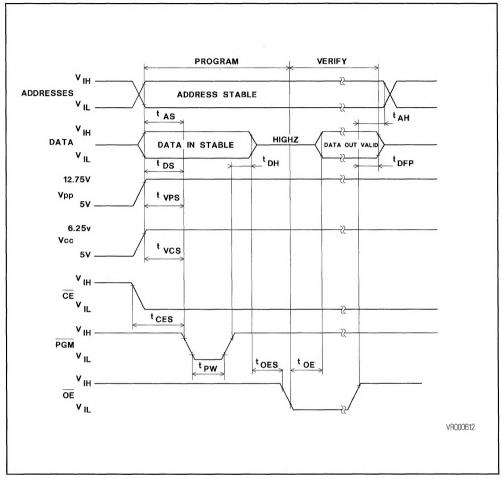
Symbol	Parameter	Test Condition	Va	lues	Unit
Symbol	Parameter	(see note 1)	Min	Max	Unit
tas	Address Setup Time		2		μs
toes	OE Setup Time		2		μs
tos	Data Setup Time		2		μs
tah	Address Hold Time		0		μѕ
tон	Data Hold Time		2		μs
t <sub>DFP(2)</sub>	Output Enable Output Float Delay		0	130	ns
tvps	V <sub>PP</sub> Setup Time		2		μs
tvcs	V <sub>CC</sub> Setup Time		2		μs
tces	CE Setup Time		2		μs
t <sub>PW</sub>	PGM Initial Program Pulse Width		95	105	μs
toe	Data Valid from OE			100	ns

NOTES: 1. Vcc must be applied simultaneously or before VPP and removed simultaneously or after VPP.

This parameter is only sampled and not 100 % tested. Output Float is defined as the point where data is no longer driven (see timing diagram).

## **PROGRAMMING OPERATION (Continued)**

## Figure 6: Programming Waveforms

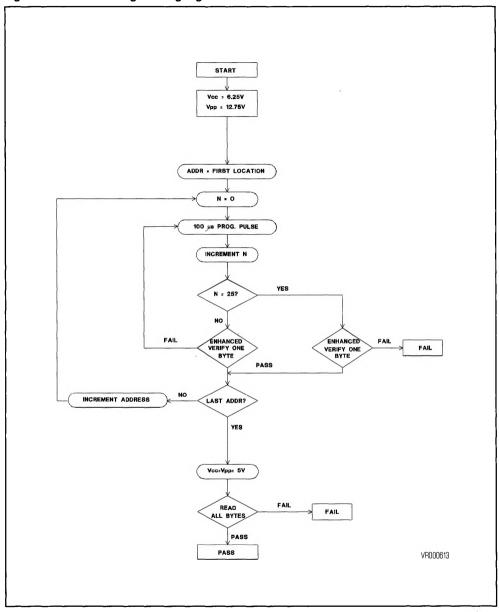


NOTES: 1. The input timing reference level is 0.8V for a  $V_{IL}$  and 2V for a  $V_{IH}$ .

 to and tope are characteristics of the device but must be accommodated by the programmer.
 When programming the M27C1000 a 0.1μF capacitor is required across V<sub>PP</sub> and GND to suppress spurious voltage transients which can damage the device.

## **PROGRAMMING OPERATION (Continued)**

## Figure 7: PRESTO II Programming Algorithm Flow Chart



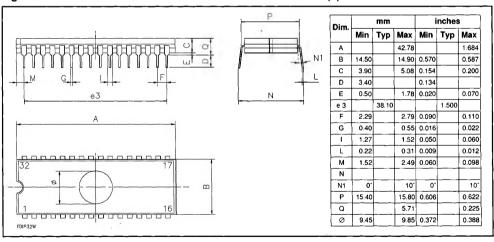
## **ORDERING INFORMATION - UV EPROM**

Part Number	Access Time	Supply Voltage	Temp. Range	Package
M27C1000 - 12XF1	120 ns	5V ± 5%	0°C to +70°C	FDIP32-W
M27C1000 - 15XF1	150 ns	5V ± 5%	0°C to +70°C	FDIP32-W
M27C1000 - 20XF1	200 ns	5V ± 5%	0°C to +70°C	FDIP32-W
M27C1000 - 25XF1	250 ns	5V ± 5%	0°C to +70°C	FDIP32-W
M27C1000 - 12F1	120 ns	5V ± 10%	0°C to +70°C	FDIP32-W
M27C1000 - 15F1	150 ns	5V ± 10%	0°C to +70°C	FDIP32-W
M27C1000 - 20F1	200 ns	5V ± 10%	0°C to +70°C	FDIP32-W
M27C1000 - 25F1	250 ns	5V ± 10%	0°C to +70°C	FDIP32-W
M27C1000 - 12XF6	120 ns	5V ± 5%	-40°C to +85°C	FDIP32-W
M27C1000 - 15XF6	150 ns	5V ± 5%	-40°C to +85°C	FDIP32-W
M27C1000 - 15F6	150 ns	5V ± 10%	-40°C to +85°C	FDIP32-W

NOTE: Consult your nearest SGS-THOMSON sales office for availability of other combination.

## PACKAGE MECHANICAL DATA

Figure 8: 32-PIN WINDOW CERAMIC DUAL IN LINE FRIT-SEAL (F)



## **ORDERING INFORMATION (OTP ROM)**

Part Number	Access Time	Supply Voltage	Temp. Range	Package
M27C1000-15XB1	150 ns	5V ± 5%	0°C to +70°C	DIP32
M27C1000-20XB1	200 ns	5V ± 5%	0°C to +70°C	DIP32
M27C1000-15B1	150 ns	5V ± 10%	0°C to +70°C	DIP32
M27C1000-20B1	200 ns	5V ± 10%	0°C to +70°C	DIP32
M27C1000-15XB6	150 ns	5V ± 5%	-40°C to +85°C	DIP32
M27C1000-15XC1	150 ns	5V ± 5%	0°C to +70°C	PLCC32
M27C1000-20XC1	200 ns	5V ± 5%	0°C to +70°C	PLCC32
M27C1000-15C1	150 ns	5V ± 10%	0°C to +70°C	PLCC32
M27C1000-20C1	200 ns	5V ± 10%	0°C to +70°C	PLCC32
M27C1000-15XC6	150 ns	5V ± 5%	-40°C to +85°C	PLCC32

NOTE: Consult your nearest SGS-THOMSON sales office for availability of other combination.

# PACKAGE MECHANICAL DATA (Continued)

Figure 9 : PLASTIC DIL 32

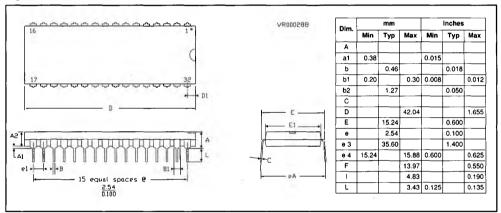


Figure 10: PLCC32-32-LEAD PLASTIC LEADED CHIP CARRIER

